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2	BRS	L2	10	("4638347 4533636 "5422504" "5280446" "5408115" "5422504" "5554869" "5734607"	USPAT	13:19
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1	IS&R	363	(257/324) CCLS	USPAT:	2003/01/14
2	BRS	21	((25/1324).0020-)	USPAT:	2003/01/14
3	BRS	35	mnos and select a gate	US-PGPUB USPAT:	2003/01/14
4	BRS	33	(mnos and select adj gate) not (((257/324).CCLS) and select adj gate)	US-PGPUB	12:10

Document ID Pages Title					Current	Current XRef	Inventor
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